

MDLM119-X REV 2A2

 Original Creation Date: 07/02/01
 Last Update Date: 07/11/01
 Last Major Revision Date:

HIGH SPEED DUAL COMPARATOR

General Description

The LM119 precision high speed dual comparator is fabricated on a single monolithic chip. It is designed to operate over a wide range of supply voltages down to a single 5V logic supply and ground. Furthermore, it has a higher gain and lower input current than other devices. The uncommitted collector of the output stage makes the LM119 compatible with RTL, DTL and TTL as well as capable of driving lamps and relays at currents up to 25mA.

Industry Part Number

LM119

Prime Die

LM119

Controlling Document

SEE FEATURES SECTION

NS Part Numbers

 LM119E-SMD
 LM119H-QMLV
 LM119H-SMD
 LM119J-QMLV
 LM119J-SMD
 LM119W-QMLV
 LM119W-SMD
 LM119WG-QMLV
 LM119WG-SMD

Processing

MIL-STD-883, Method 5004

Quality Conformance Inspection

MIL-STD-883, Method 5005

Subgrp	Description	Temp (°C)
1	Static tests at	+25
2	Static tests at	+125
3	Static tests at	-55
4	Dynamic tests at	+25
5	Dynamic tests at	+125
6	Dynamic tests at	-55
7	Functional tests at	+25
8A	Functional tests at	+125
8B	Functional tests at	-55
9	Switching tests at	+25
10	Switching tests at	+125
11	Switching tests at	-55

Features

- Two independent comparators.
- Operates from a single 5V supply.
- Typically 80nS response time at $\pm 15V$.
- Minimum fan-out of 2 each side.
- Maximum input current of 1uA over temperature.
- Inputs and outputs can be isolated from system ground.
- High common mode slew rate.

- CONTROLLING DOCUMENTS

LM119E-SMD	86014012A
LM119H-QMLV	5962-9679801VIA
LM119H-SMD	8601401IA
LM119J-QMLV	5962-9679801VCA
LM119J-SMD	8601401CA
LM119W-QMLV	5962-9679801VHA
LM119W-SMD	8601401HA
LM119WG-QMLV	5962-9679801VXA
LM119WG-SMD	8601401X

Although designed primarily for applications requiring operation from digital logic supplies, the LM119 is fully specified for power supplies up to $\pm 15V$. It features faster response than the LM111 at the expense of higher power dissipation. However, the high speed, wide operating voltage range and low package count make the LM119 much more versatile than older devices.

(Absolute Maximum Ratings)

(Note 1)

Total Supply Voltage	36V
Output to Negative Supply Voltage	36V
Ground to Negative Supply Voltage	25V
Ground to Positive Supply Voltage	18V
Differential Input Voltage	±5V
Input Voltage (Note 3)	±15V
Power Dissipation (Note 2)	500mW
Output Short Circuit Duration	10 seconds
Maximum Junction Temperature	150 C
Storage Temperature Range	-65 C to 150 C
Lead Temperature (Soldering, 10 seconds)	260 C
Thermal Resistance	
ThetaJA	
E Package (Still Air)	89 C/W
E Package (500LF/Min Air flow)	63 C/W
H Package (Still Air)	162 C/W
H Package (500LF/Min Air flow)	88 C/W
J Package (Still Air)	94 C/W
J Package (500LF/Min Air flow)	52 C/W
W Package (Still Air)	215 C/W
W Package (500LF/Min Air flow)	132 C/W
WG Package (Still Air)	215 C/W
WG Package (500LF/Min Air flow)	132 C/W
ThetaJC	
E Package	5 C/W
H Package	31 C/W
J Package	11 C/W
W Package	13 C/W
WG Package	13 C/W
Package Weight	
E Package	TBD
H Package	TBD
J Package	TBD
W Package	TBD
WG Package	225mg
ESD Tolerance (Note 4)	800V

- Note 1: Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is functional, but do not guarantee specific performance limits. For guaranteed specifications and test conditions, see the Electrical Characteristics. The guaranteed specifications apply only for the test conditions listed. Some performance characteristics may degrade when the device is not operated under the listed test conditions.
- Note 2: The maximum power dissipation must be derated at elevated temperatures and is dictated by T_{jmax} (maximum junction temperature), θ_{JA} (package junction to ambient thermal resistance), and T_A (ambient temperature). The maximum allowable power dissipation at any temperature is $P_{dmax} = (T_{jmax} - T_A)/\theta_{JA}$ or the number given in the Absolute Maximum Ratings, whichever is lower.
- Note 3: For supply voltages less than $\pm 15V$ the absolute maximum input voltage is equal to the supply voltage.
- Note 4: Human body model, 1.5K Ohm in series with 100pF.

Recommended Operating Conditions

Operating Temperature Range

$$-55\text{ C} \leq T_A \leq 125\text{ C}$$

Electrical Characteristics

DC PARAMETERS:

(The following conditions apply to all the following parameters, unless otherwise specified.)

DC: $V_{cm} = 0V$

SYMBOL	PARAMETER	CONDITIONS	NOTES	PIN-NAME	MIN	MAX	UNIT	SUB-GROUPS
Icc+	Positive Supply Current	$\pm V_{cc} = \pm 15V$				11	mA	1
						11.5	mA	2, 3
Icc-	Negative Supply Current	$\pm V_{cc} = \pm 15V$			-4.2		mA	1
					-4.5		mA	2
					-6		mA	3
Ileak	Output Leakage Current	$+V_{cc} = 15V, -V_{cc} = -1V, V_{gnd} = 0V, V_{out} = 35V$	1			1.8	uA	1
			1			10	uA	2, 3
Iib	Input Bias Current	$\pm V_{cc} = \pm 15V$				0.475	uA	1
						0.95	uA	2, 3
		$V_{cc} = 5V$	2			0.475	uA	1
			2			.95	uA	2, 3
Vio	Input Offset Voltage	$V_{cc} = 5V, V_{cm} = 1V, R_s \leq 5K$	2		-3.8	3.8	mV	1
			2		-6.8	6.8	mV	2, 3
		$V_{cc} = 5V, V_{cm} = 3V, R_s \leq 5K$	2		-3.8	3.8	mV	1
			2		-6.8	6.8	mV	2, 3
		$\pm V_{cc} = \pm 15V, V_{cm} = 12V, R_s \leq 5K$			-3.8	3.8	mV	1
					-6.8	6.8	mV	2, 3
		$\pm V_{cc} = \pm 15V, V_{cm} = -12V, R_s \leq 5K$			-3.8	3.8	mV	1
					-6.8	6.8	mV	2, 3
Iio	Input Offset Current	$V_{cc} = 5V, V_{cm} = 1V$	2		-75	75	nA	1
			2		-100	100	nA	2, 3
		$V_{cc} = 5V, V_{cm} = 3V$	2		-75	75	nA	1
			2		-100	100	nA	2, 3
		$\pm V_{cc} = \pm 15V, V_{cm} = 12V$			-75	75	nA	1
					-100	100	nA	2, 3
		$\pm V_{cc} = \pm 15V, V_{cm} = -12V$			-75	75	nA	1
					-100	100	nA	2, 3
Vi	Input Voltage Range	$V_{cc} = 5V$	2, 3		1	3	V	1, 2, 3
		$V_{cc} = \pm 15V$	3		-12	12	V	1, 2, 3

Electrical Characteristics

DC PARAMETERS: (Continued)

(The following conditions apply to all the following parameters, unless otherwise specified.)

DC: $V_{cm} = 0V$

SYMBOL	PARAMETER	CONDITIONS	NOTES	PIN-NAME	MIN	MAX	UNIT	SUB-GROUPS
Vsat	Output Saturation Voltage	$V_{cc} = \pm 15V$, $I_{out} = 25mA$, $V_{in} \leq -5mV$	1			1.5	V	1, 2, 3
		$+V_{cc} = 3.5V$, $-V_{cc} = -1V$, $V_{in} \leq -6mV$, $I_{sink} \leq 3.2mA$				0.4	V	1, 2
						0.6	V	3
Av	Voltage Gain	$\pm V_{cc} = \pm 15V$, $\Delta V_{out} = 12V$	4		10.5		K	4
			4		10		K	5, 6
		$V_{cc} = 5V$, $\Delta V_{out} = 4.5V$	2, 4		8		K	4
			2, 4		5		K	5
			2, 4		5.8		K	6
CMRR	Common Mode Rejection Ratio	$\pm V_{cc} = \pm 15V$, $V_{cm} = \pm 12V$			80		dB	4

DC PARAMETERS: DRIFT VALUES

(The following conditions apply to all the following parameters, unless otherwise specified.)

DC: $V_{cm} = 0V$. Delta calculations performed on JAN S and QMLV devices at group B, subgroup 5 ONLY.

Icc+	Positive Supply Current	$\pm V_{cc} = \pm 15V$			-1	1	mA	1
Icc-	Negative Supply Current	$\pm V_{cc} = \pm 15V$			-0.5	0.5	mA	1
Vio	Input Offset Voltage	$V_{cc} = 5V$, $V_{cm} = 1V$, $R_s \leq 5K$			-0.4	0.4	mV	1

Note 1: $V_{in} \geq 8mV$ at extremes for I_{leak} and $V_{in} \leq -8mV$ at extremes for V_{sat} (V_{in} to exceed V_{os}).

Note 2: 5 Volt differential across $+V_{cc}$ and $-V_{cc}$.

Note 3: Parameter guaranteed by V_{io} and I_{io} tests.

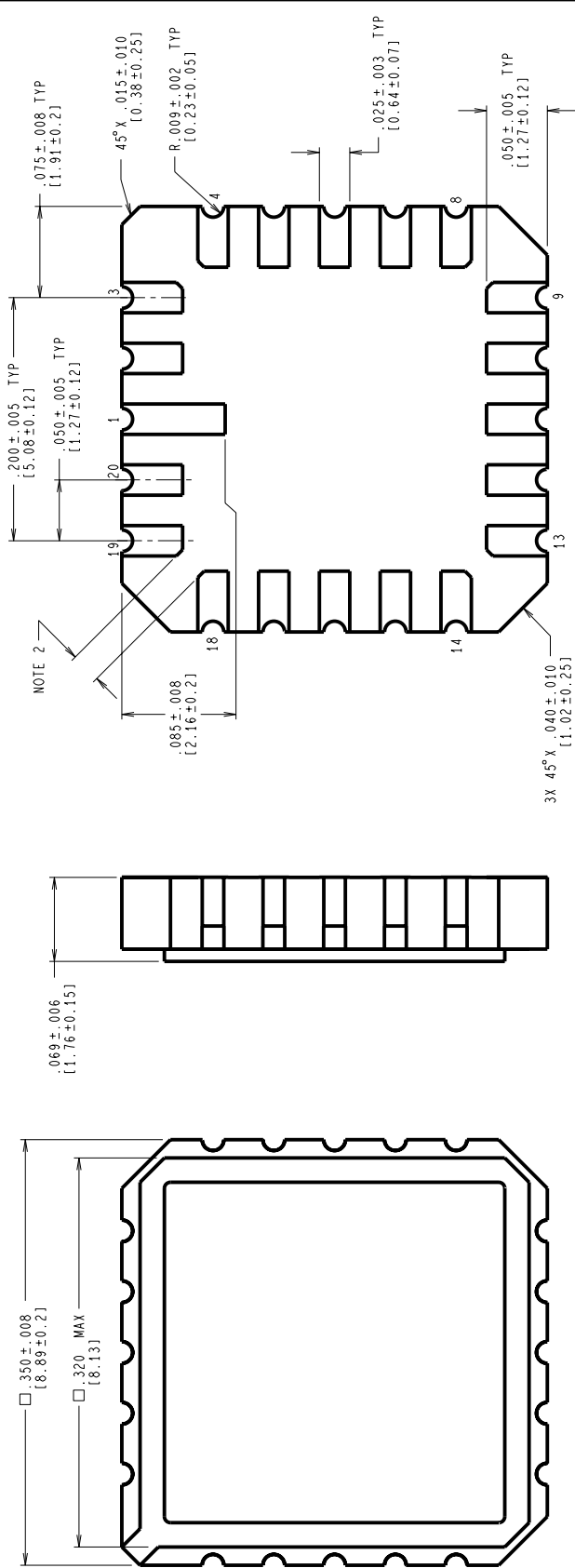
Note 4: $K = V/mV$.

Graphics and Diagrams

GRAPHICS#	DESCRIPTION
06142HRA3	LCC (E), TYPE C, 20 TERMINAL (B/I CKT)
08906HRB3	METAL CAN (H), 10 LEAD (B/I CKT)
09078HRB3	CERPACK (W), 10 LEAD (B/I CKT)
09641HRA2	CERDIP (J), 14 LEAD (B/I CKT)
E20ARE	LCC (E), TYPE C, 20 TERMINAL (P/P DWG)
H10CRF	METAL CAN (H), TO-100, 10LD, .230 DIA PC (P/P DWG)
J14ARH	CERDIP (J), 14 LEAD (P/P DWG)
P000182A	CERDIP (J), 14 LEAD (PINOUT)
P000196A	LCC (E), 20 LEAD (PINOUT)
P000197A	METAL CAN (H), TO-100, 10 LD, .230 DIA PC (PINOUT)
P000198A	CERPACK (W), 10 LEAD (PINOUT)
P000237A	CERAMIC SOIC (WG), 10 LEAD (PINOUT)
W10ARG	CERPACK (W), 10 LEAD (P/P DWG)
WG10ARC	CERAMIC SOIC (WG), 10 LEAD (P/P DWG)

See attached graphics following this page.

REVISIONS			
LTR	DESCRIPTION	E.C.N.	DATE
E	REVISE AND REDRAW	10005	02/10/94 DEG/



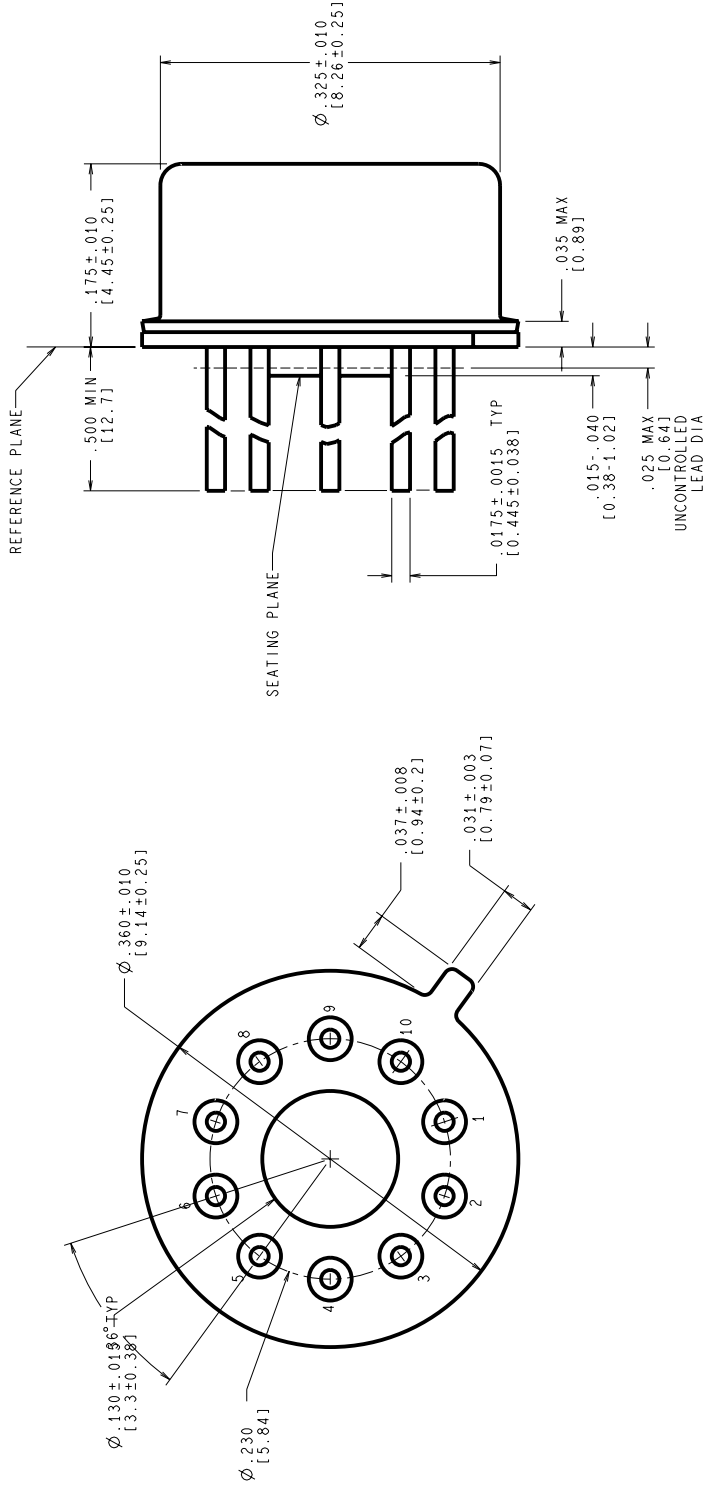
CONTROLLING DIMENSION IS INCH
VALUES IN [] ARE MILLIMETERS

- NOTES: UNLESS OTHERWISE SPECIFIED.
- LEAD FINISH TO BE ONE OF THE FOLLOWING:
 - 50 MICRONS/12.7 MICROMETERS MINIMUM GOLD PLATING OVER 50-350 MICRONS/1.27-8.89 MICROMETERS NICKEL.
 - SOLDER DIP.
 - SOLDER THICKNESS PER LATEST REVISION OF MIL-STD-1835.
 - CORNER PADS MAY HAVE A 45° X $.020$ IN/0.51mm MAXIMUM CHAMFER TO ACCOMPLISH THE .015 IN/0.38mm DIMENSION.
 - REFERENCE JEDEC REGISTRATION MS-004, VARIATION CB, DATED 7/90.

MIL/AERO CONFIGURATION CONTROL

APPROVALS		DATE	NATIONAL SEMICONDUCTOR CORPORATION	
DESIGN	Design Grady	02/10/94	2000 Semiconductor Drive, Santa Clara, CA 95052-8090	
ESTG. CHK.			LEADLESS CHIP CARRIER, TYPE C, 20 TERMINAL	
ENGR. CHK.				
APPROVAL				
PROJECTION		SCALE	SIZE	REV
		N/A	C	MKT-E20A
		DO NOT SCALE DRAWING		E
				SHEET 1 of 1

REVISIONS			
LTR	DESCRIPTION	E.C.N.	DATE
F	REVISE & REDRAW PER CURRENT STANDARD; UPDATE MIL/AERO STAMP & TITLE.	11003	06/26/95
			MS/



CONTROLLING DIMENSION IS INCH
VALUES IN [] ARE MILLIMETERS

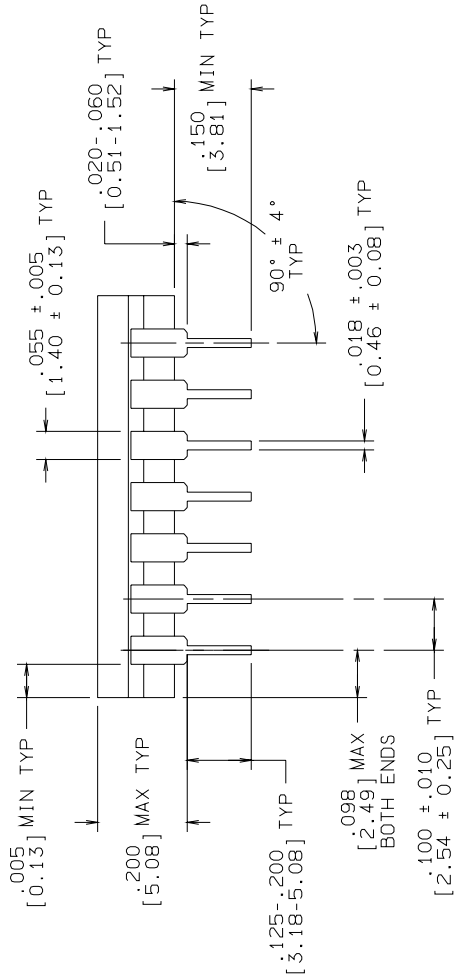
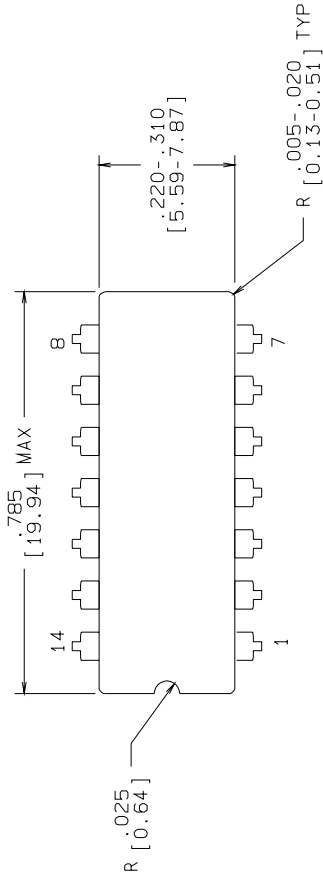
MIL-I-38535
CONFIGURATION CONTROL

NOTES: UNLESS OTHERWISE SPECIFIED

- LEADS TO BE LOCATED WITHIN .007 IN/ 0.18 mm OF THEIR TRUE POSITIONS RELATIVE TO A MAXIMUM WIDTH TAB.
- STANDARD METAL CAN TYPE: SOLID BASE WITH CERAMIC STANDOFF.
- APPLIES TO MIL-AERO AND LINEAR PRODUCTS.
- REFERENCE JEDEC REGISTRATION TO-100, JEDEC PUBLICATION No. 95.

APPROVALS		DATE	National Semiconductor	
DESIGN	MARIA SUICH	06/26/95	2000 Semiconductor dr., Santa Clara, CA 95052-8000	
DATE	CHK.		METAL CAN, TO-100, 10 LEAD, .230 DIA P.C.	
ENTER	CHK.			
PROJECTION		SCALE	SIZE	DRAWING NUMBER
		N/A	C	MKT-H10C
		DO NOT SCALE	DRAWING	SHEET 1 of 1

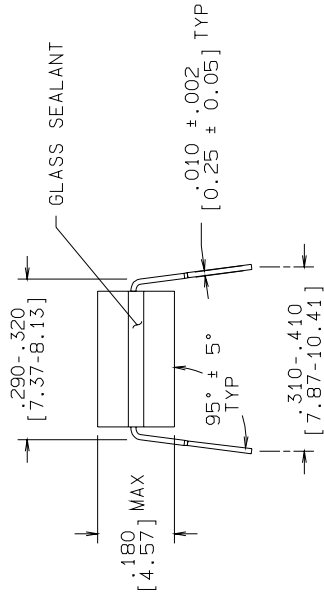
R E V I S I O N S				
LTR	DESCRIPTION	E.C.N.	DATE	BY/APP'D
H	REVISE PER CURRENT STD; REDRAW	10001	09/15/93	TL/



CONTROLLING DIMENSION: INCH

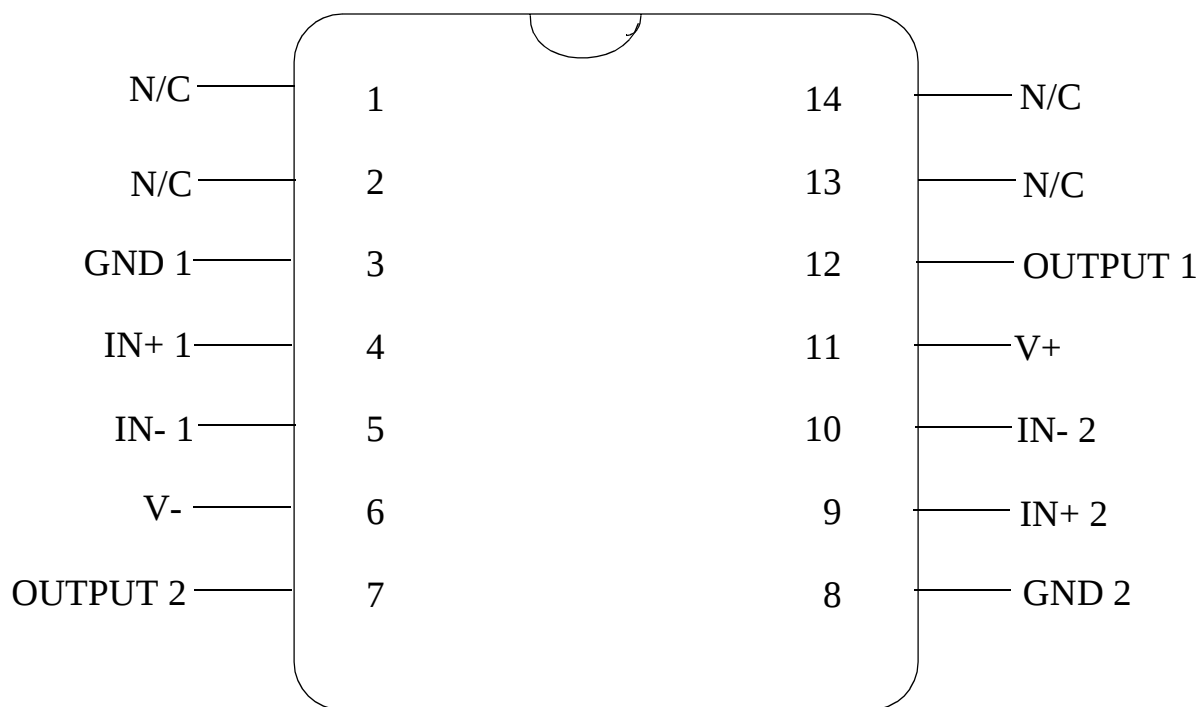
NOTES: UNLESS OTHERWISE SPECIFIED

1. LEAD FINISH TO BE 200 MICROMETERS / 5.08 MICROMETERS MINIMUM SOLDER MEASURED AT THE CREST OF THE MAJOR FLATS.
2. JEDEC REGISTRATION MO-036, VARIATION AB, DATED 04/1981.



MIL/AERO MIL-M-38510
CONFIGURATION CONTROL CONFIGURATION CONTROL

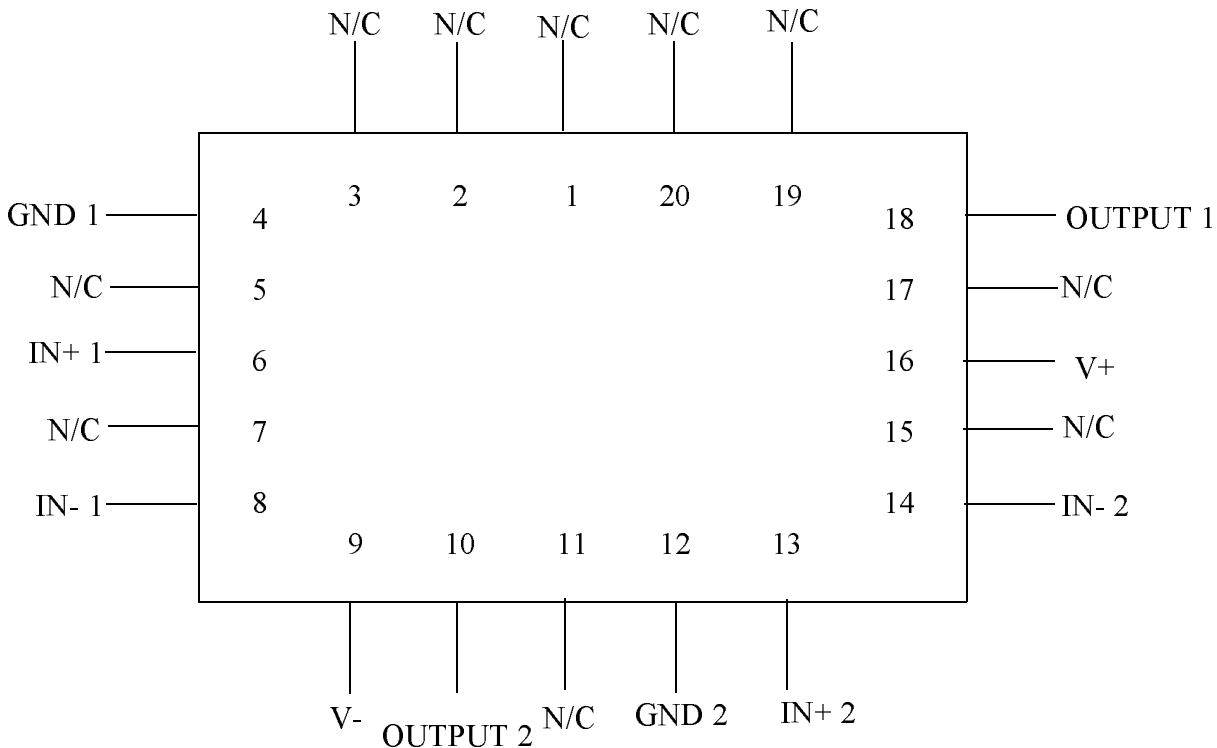
APPROVALS	DATE	NATIONAL SEMICONDUCTOR CORPORATION		
DRAWN LEQUANG	09/15/93	2900 Semiconductor Drive, Santa Clara, CA 95052-8090		
DFTG. CHK.				
ENGR. CHK.				
APPROVAL		CERDIP (J) , 14 LEAD,		
 PROJECTION 1 INCH [25.4]	SCALE	SIZE	DRAWING NUMBER	REV
	N/A	B	MKT-J14A	H
DO NOT SCALE DRAWING		SHEET	1	OF 1



LM119J
 14 - LEAD DIP
 CONNECTION DIAGRAM
 TOP VIEW
 P000182A



National Semiconductor™
 MIL/AEROSPACE OPERATIONS
 2900 SEMICONDUCTOR DRIVE
 SANTA CLARA, CA 95050



LM119E

20 - LEAD LCC

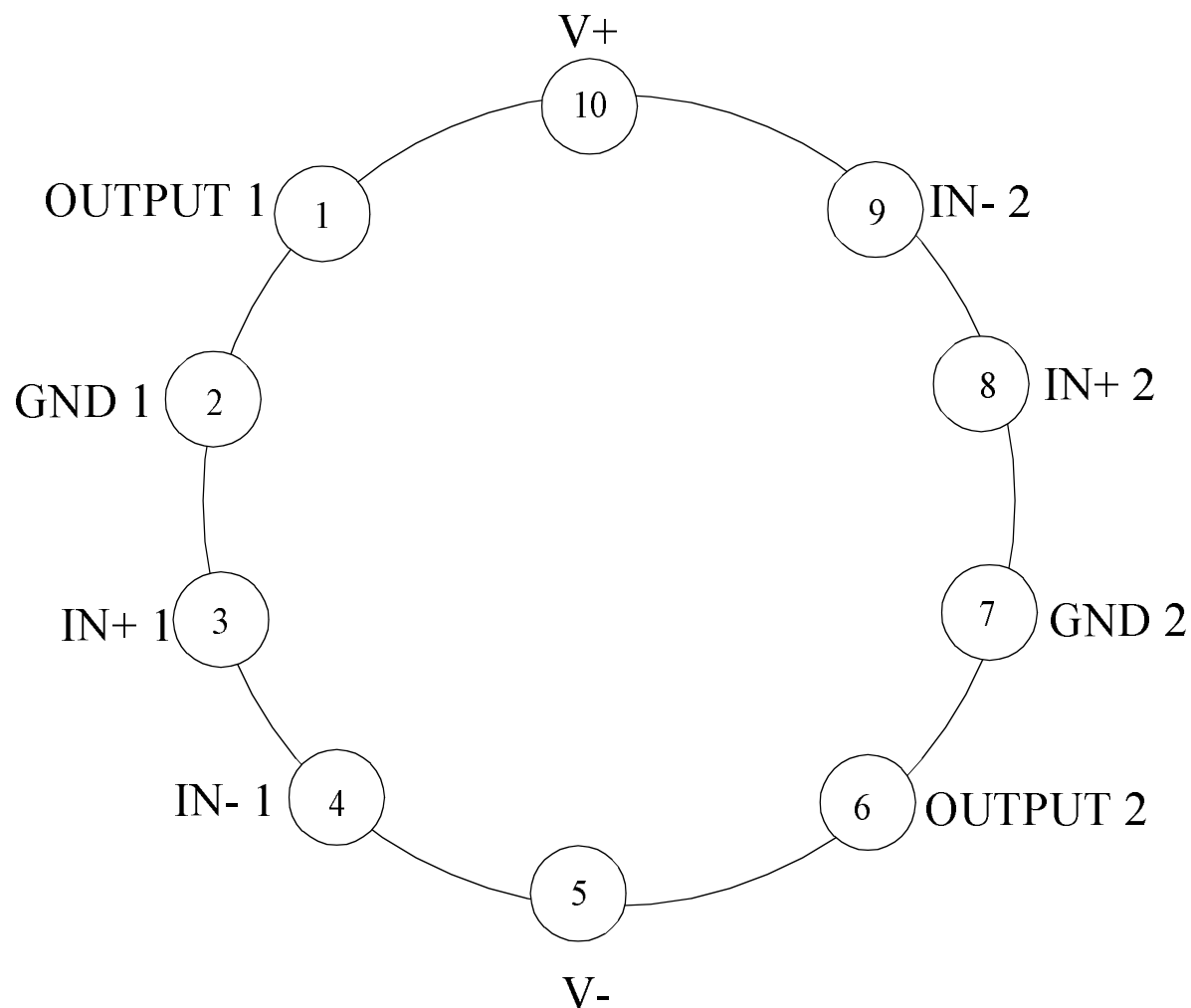
CONNECTION DIAGRAM

TOP VIEW

P000196A



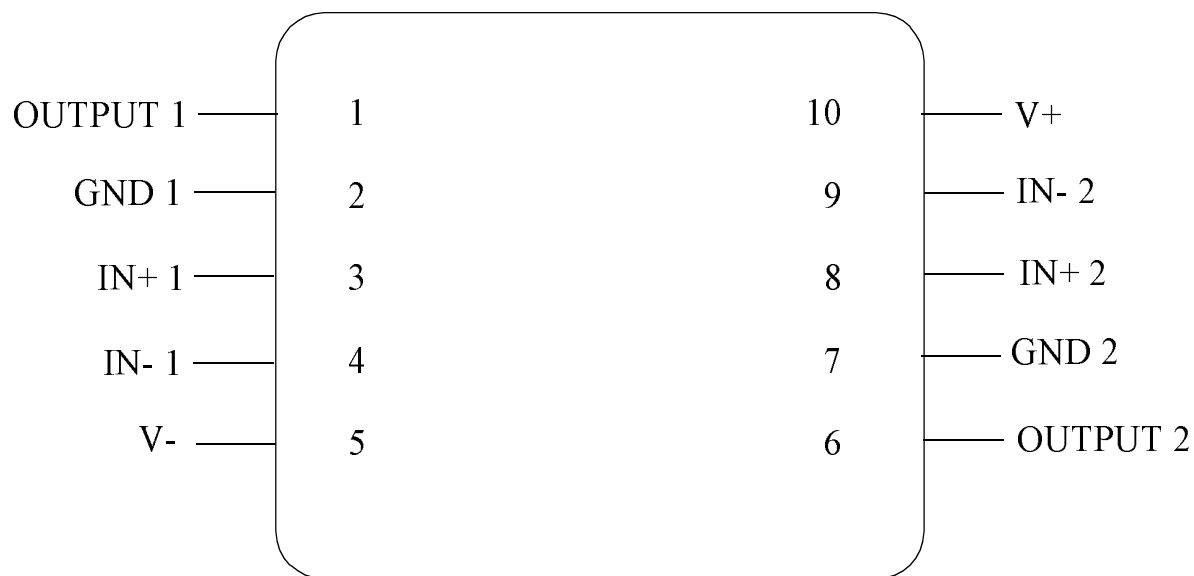
National Semiconductor™
MIL/AEROSPACE OPERATIONS
2900 SEMICONDUCTOR DRIVE
SANTA CLARA, CA 95050



LM119H
10 - PIN METAL CAN
CONNECTION DIAGRAM
TOP VIEW
P000197A



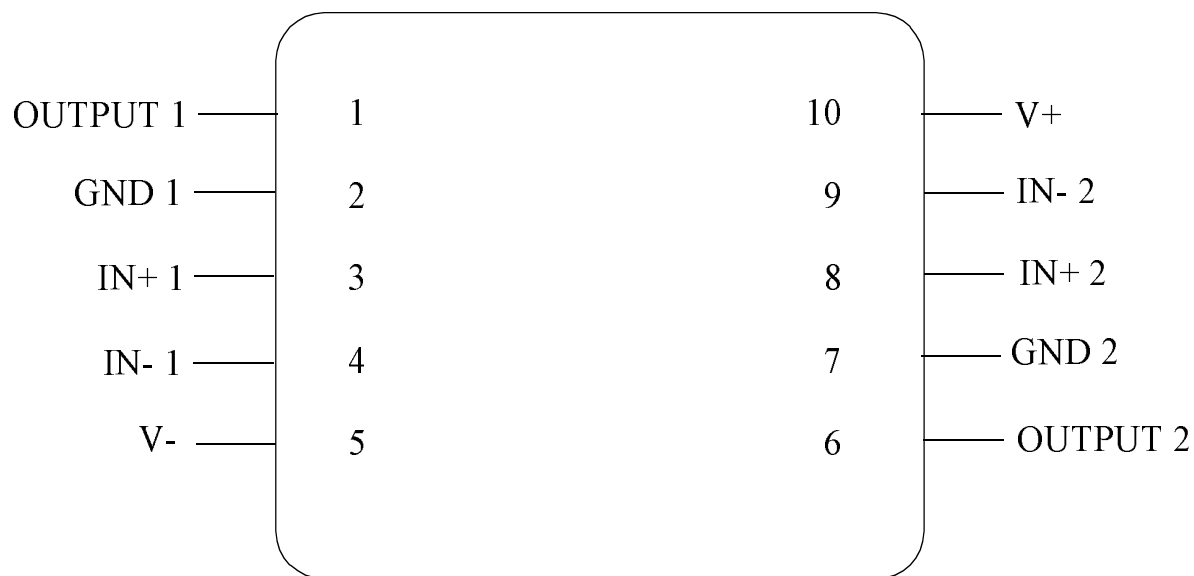
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MIL/AEROSPACE OPERATIONS
2900 SEMICONDUCTOR DRIVE
SANTA CLARA, CA 95050



LM119W
10 - LEAD CERPAC
CONNECTION DIAGRAM
TOP VIEW
P000198A



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 MIL/AEROSPACE OPERATIONS
 2900 SEMICONDUCTOR DRIVE
 SANTA CLARA, CA 95050

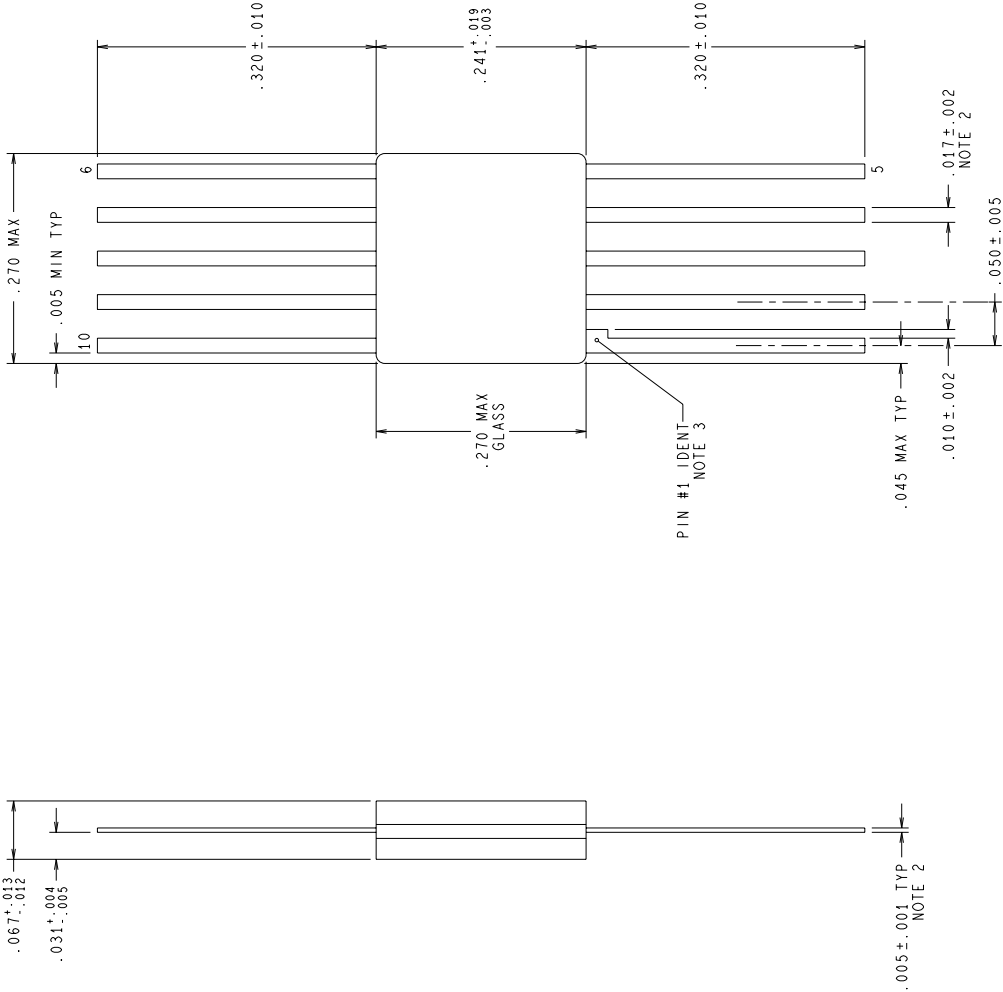


LM119WG
10 - LEAD CERAMIC SOIC
CONNECTION DIAGRAM
TOP VIEW
P000237A



National Semiconductor™
 MIL/AEROSPACE OPERATIONS
 2900 SEMICONDUCTOR DRIVE
 SANTA CLARA, CA 95050

REVISIONS			
LTR	DESCRIPTION	E.C.N.	DATE
F	REVISE AND REDRAW PER NEW STANDARD.	10510	07/28/94 DEG/AEP
G	.017±.002 WAS .017±.020.	10654	10/21/94 DEG/



NOTES: UNLESS OTHERWISE SPECIFIED.

1. LEAD FINISH: SOLDER DIPPED WITH Sn60 OR Sn63 SOLDER CONFORMING TO MIL-M-38510 TO A MINIMUM THICKNESS OF 200 MICROINCHES. SOLDER MAY BE APPLIED OVER LEAD BASIS METAL OR Sn PLATE.
2. MAXIMUM LIMIT MAY BE INCREASED BY .003 INCHES AFTER LEAD FINISH APPLIED.
3. LEAD 1 IDENTIFICATION SHALL BE:
 - a) A NOTCH OR OTHER MARK WITHIN THIS AREA
 - b) A TAB ON LEAD 1, EITHER SIDE
4. REFERENCE JEDEC REGISTRATION M0-003, VARIATION AG, DATED 06/01/76.

MIL/AERO
CONFIGURATION CONTROL

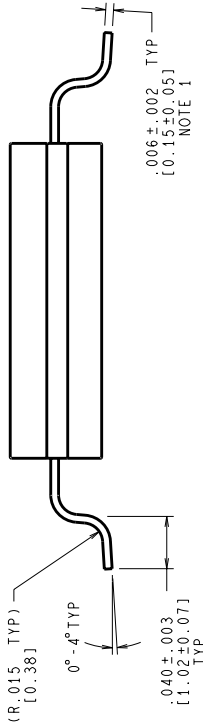
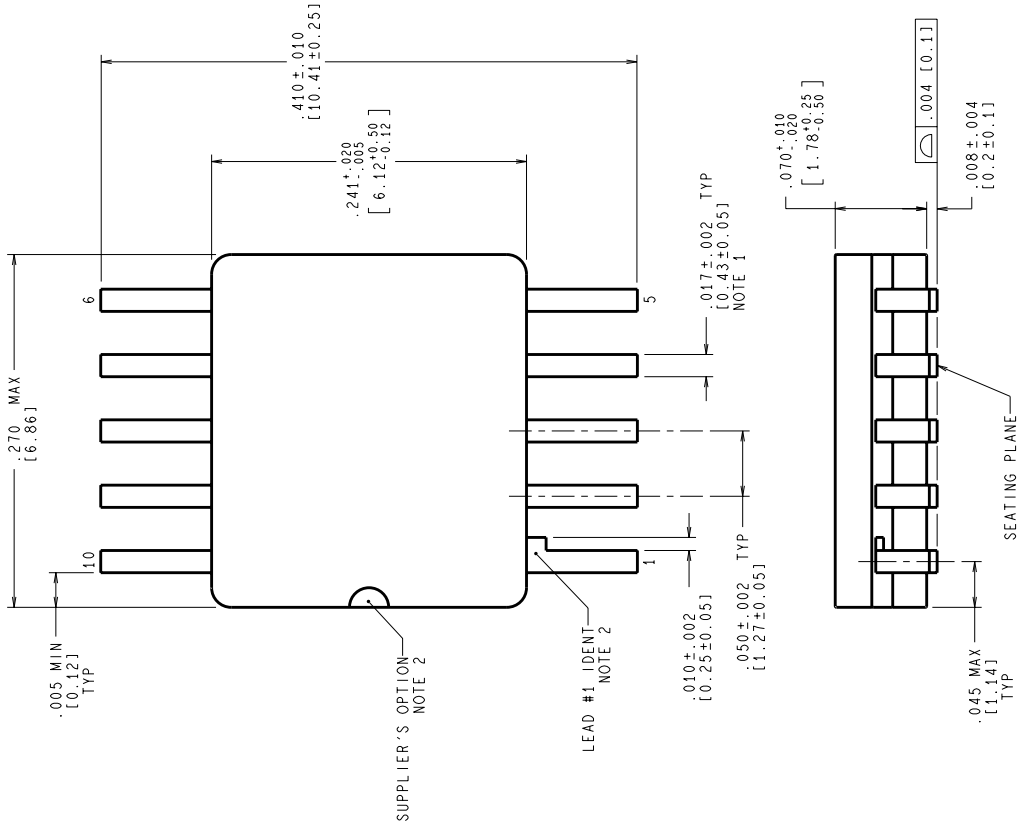
MIL-M-38510
CONFIGURATION CONTROL

APPROVALS		DATE	
DRWN	<i>D. F. Grady</i>	07/28/94	
DFTG	CHK.		
ENGR	CHK.		
PROJECTION			
SCALE	N/A	SIZE	C
DRAWING NUMBER	MKT-W10A		
REV	G		
DO NOT SCALE DRAWING		SHEET 1 of 1	

 *National Semiconductor*
2000 Semiconductor dr., Santa Clara, CA 95052-8090

CERPACK, 10 LEAD

REVISIONS				
LTR	DESCRIPTION	E.C.N.	DATE	BY/APP'D
A	RELEASE TO DOCUMENT CONTROL	11374	02/29/1996	MS/KH
B	LD PITCH TOL WAS $\pm .005$; CHANGE LD RADIUS TO REF DIM; REMOVE THE OTHER R .006 $\pm .002$ DIM .040 $\pm .003$ WAS .037 $\pm .003$	11441	04/19/1996	MS/KH
C	R .015(0.38) WAS R .006(0.15)	11838	10/08/1997	TL/



CONTROLLING DIMENSION IS INCH
VALUES IN | | ARE MILLIMETERS

MIL-PRF-38535 CONFIGURATION CONTROL

NOTES: UNLESS OTHERWISE SPECIFIED

- LEAD FINISH: SOLDER DIPPED WITH Sn60 OR Sn63 SOLDER CONFORMING TO MIL-PRF-38535 TO A MINIMUM THICKNESS OF 200 MICRONS/ 5.08 MICROMETERS. SOLDER MAY BE APPLIED OVER LEAD BASIS METAL OR Sn PLATE. MAXIMUM LIMIT MAY BE INCREASED BY .003 IN/ 0.08mm AFTER LEAD FINISH APPLIED.
- LEAD 1 IDENTIFICATION SHALL BE:
 - A NOTCH OR OTHER MARK WITHIN THIS AREA
 - A TAB ON LEAD 1, EITHER SIDE
- NO JEDEC REGISTRATION AS OF FEBRUARY 1996.

APPROVALS	DATE	National Semiconductor	
DESIGN	02/29/96	2000 Semiconductor dr., Santa Clara, CA 95052-8000	
DRW		CERPACK, 10 LEAD, GULL WING	
DATE			
CHK			
CHK			
PROJECTION			
SCALE	N/A	SIZE	C
DRAWING NUMBER	(SC)MKT-WG10A	REV	C
DO NOT SCALE DRAWING			
SHEET 1 of 1			

Revision History

Rev	ECN #	Rel Date	Originator	Changes
0B0	M0001371	02/25/98	Barbara Lopez	Added Power Dissipation - Note 2 in Absolute section. Renumbered all other notes. Archive MDS - MDLM119-X Rev. 0A0. Release MDS - MDLM119-X Rev. 0B0.
0C1	M0002726	12/06/99	Barbara Lopez	Update MDS: MDLM119-X Rev. 0B0 to MDLM119-X Rev. 0C1. Added WG package to MDS. Added MKT outline, Burn-In CKT and Pinouts.
1C1	M0003596	12/06/99	Rose Malone	Archive MDLM119-X, Rev. 0C1. MDS replaced by MDLM119-X-RH, Rev. 0A0. MDS is being archived as Rev. 1C1.
2A2	M0003821	07/11/01	Rose Malone	De-Archived MDS: MDLM119-X, Re-Instate back into system at Rev. 2A2. Removed Rad Devices, MDLM119-X references Non Rad Devices ONLY. MDLM119-X, Rev. 2A2 replaces MDLM119-X-RH